

ABSTRACT OF THE DISCLOSURE

An over-driven access method and device for ferroelectric memory.

When accessing the data stored in a ferroelectric memory, the invention further provides an over-driven current to slightly reduce/raise the voltages in
5 bit lines BL and BL' to further enlarge the voltage difference therebetween after having raised the plate-line /bit-line voltage using the plate-line /bit-line driven method.

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